

## 1. General description

Planar passivated very sensitive gate four quadrant triac in a SOT223 (SC-73) surface-mountable plastic package intended for applications requiring direct interfacing to logic level ICs and low power gate drivers.

## 2. Features and benefits

- Direct interfacing to logic level ICs
- Direct interfacing to low power gate drive circuits
- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Surface-mountable package
- Triggering in all four quadrants
- Very sensitive gate

## 3. Applications

- General purpose low power motor control
- Home appliances
- Industrial process control
- Low power AC Fan controllers

## 4. Quick reference data

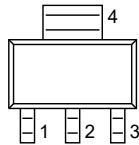
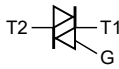
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{sp} \leq 105\text{ °C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	-	1	A
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	-	8	A
		full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 16.7\text{ ms}$	-	-	8.5	A
$T_j$	junction temperature		-	-	125	°C
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 9</a>	-	-	5	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 9</a>	-	-	5	mA

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 9</a>	-	-	5	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G+; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 9</a>	-	-	7	mA
$I_H$	holding current	$V_D = 12\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 11</a>	-	-	10	mA
$V_T$	on-state voltage	$I_T = 1.4\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 12</a>	-	1.3	1.6	V
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$ ; $T_j = 110\text{ }^\circ\text{C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit; <a href="#">Fig. 14</a>	20	-	-	V/ $\mu\text{s}$
$dV_{com}/dt$	rate of change of commutating voltage	$V_D = 400\text{ V}$ ; $T_j = 110\text{ }^\circ\text{C}$ ; $dI_{com}/dt = 0.44\text{ A/ms}$ ; gate open circuit	1	-	-	V/ $\mu\text{s}$

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	 <p>SC-73 (SOT223)</p>	 <p>sym051</p>
2	T2	main terminal 2		
3	G	gate		
4	T2	main terminal 2		

## 6. Ordering information

Table 3. Ordering information

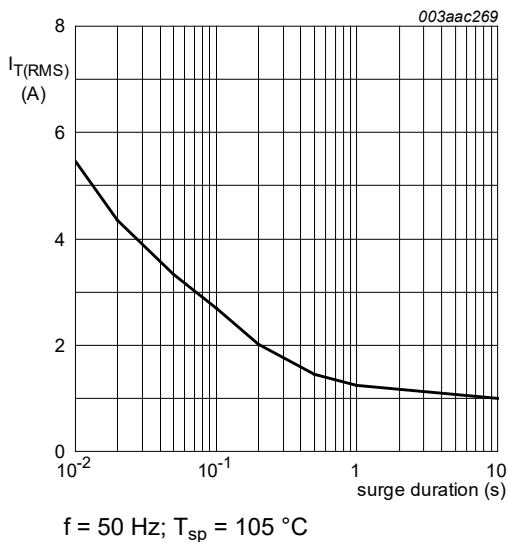
Type number	Package		
	Name	Description	Version
Z0107NN	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223

## 7. Limiting values

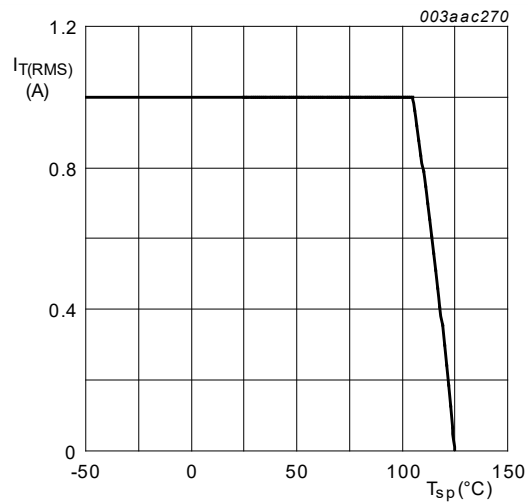
**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{sp} \leq 105\text{ °C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	1	A
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(\text{init})} = 25\text{ °C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	8	A
		full sine wave; $T_{j(\text{init})} = 25\text{ °C}$ ; $t_p = 16.7\text{ ms}$	-	8.5	A
$I^2t$	$I^2t$ for fusing	$t_p = 10\text{ ms}$ ; SIN	-	0.32	A <sup>2</sup> s
$di_T/dt$	rate of rise of on-state current	$I_G = 20\text{ mA}$ ; T2+ G+	-	50	A/ $\mu$ s
		$I_G = 20\text{ mA}$ ; T2+ G-	-	50	A/ $\mu$ s
		$I_G = 20\text{ mA}$ ; T2- G-	-	50	A/ $\mu$ s
		$I_G = 20\text{ mA}$ ; T2- G+	-	20	A/ $\mu$ s
$I_{GM}$	peak gate current		-	1	A
$P_{GM}$	peak gate power		-	2	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.1	W
$T_{stg}$	storage temperature		-40	150	°C
$T_j$	junction temperature		-	125	°C



**Fig. 1. RMS on-state current as a function of surge duration; maximum values**



**Fig. 2. RMS on-state current as a function of solder point temperature; maximum values**

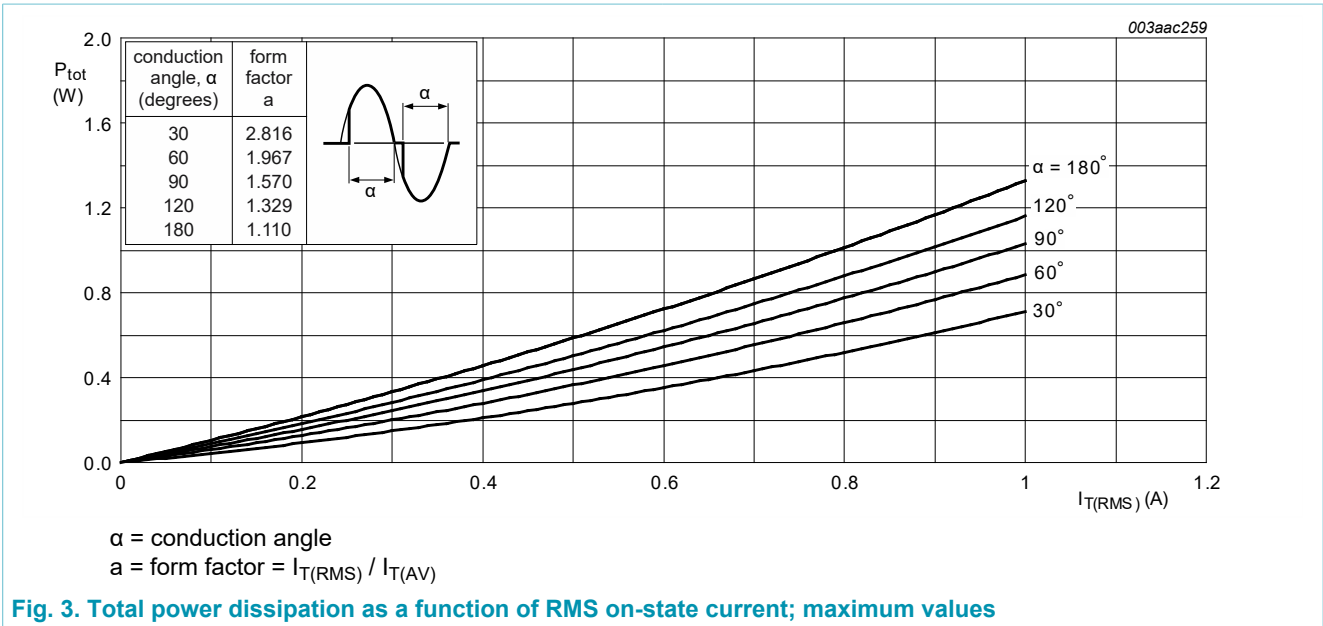


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

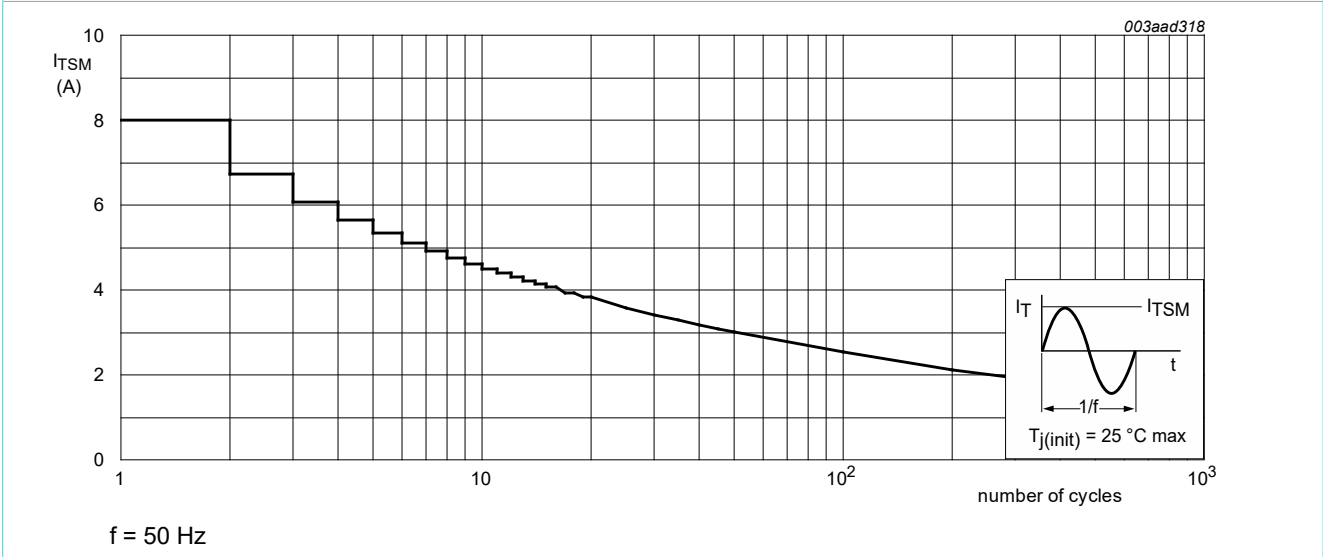
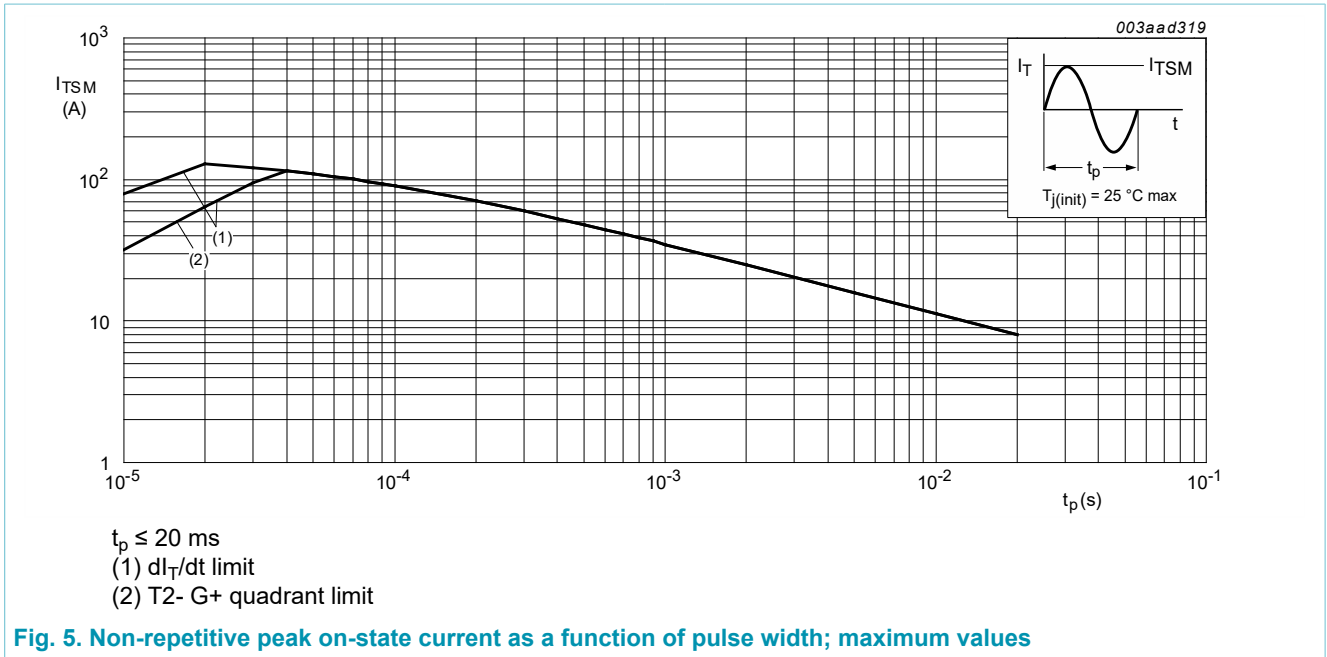


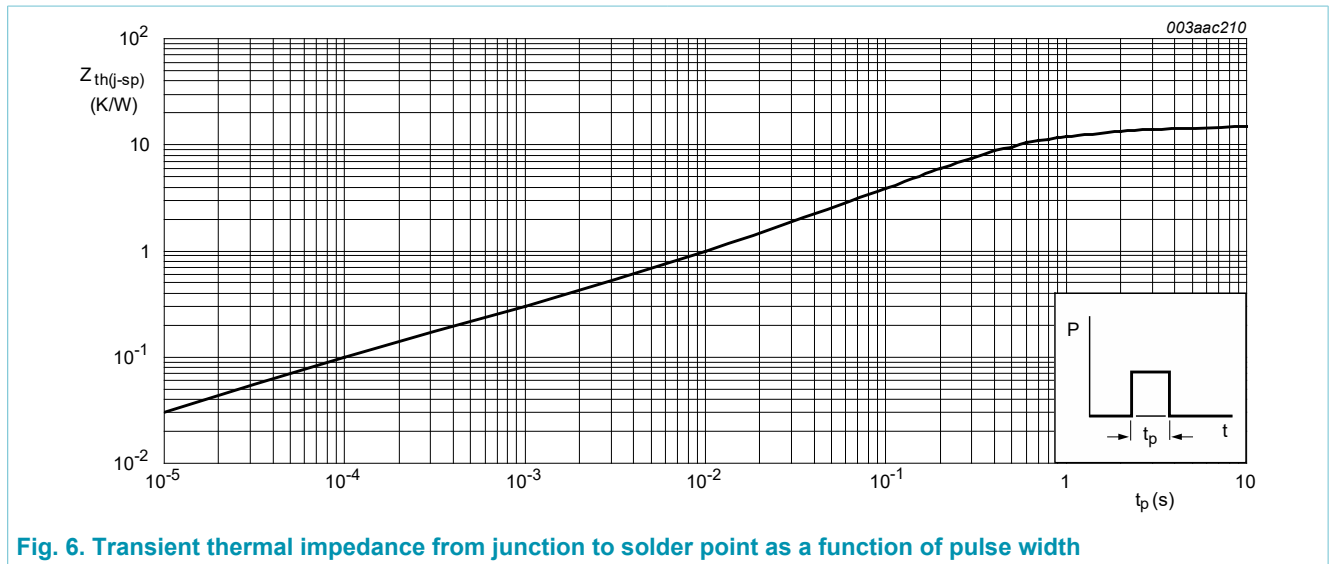
Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

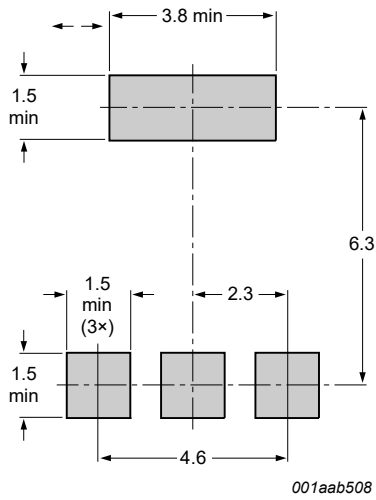


## 8. Thermal characteristics

Table 5. Thermal characteristics

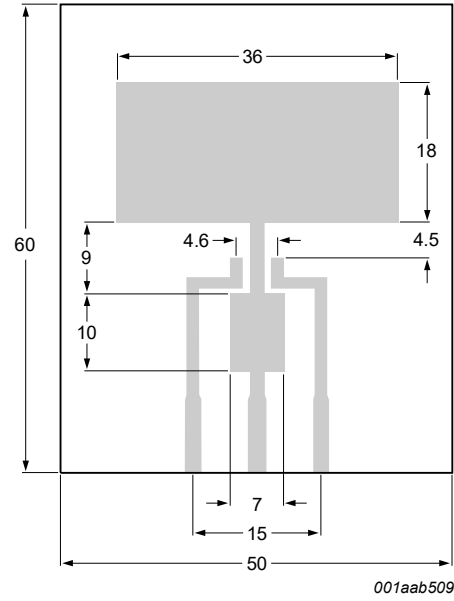
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	full cycle; <a href="#">Fig. 6</a>	-	-	15	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	full cycle; printed circuit board mounted; minimum footprint; <a href="#">Fig. 7</a>	-	156	-	K/W
		full cycle; printed circuit board mounted; pad area; <a href="#">Fig. 8</a>	-	70	-	K/W





All dimensions are in mm

**Fig. 7. Minimum footprint SOT223**



All dimensions are in mm

Printed circuit board:

FR4 epoxy glass (1.6 mm thick), copper laminate (35 um thick)

**Fig. 8. Printed circuit board pad area: SOT223**

## 9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
I <sub>GT</sub>	gate trigger current	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <a href="#">Fig. 9</a>	-	-	5	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; <a href="#">Fig. 9</a>	-	-	5	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; <a href="#">Fig. 9</a>	-	-	5	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G+; T <sub>j</sub> = 25 °C; <a href="#">Fig. 9</a>	-	-	7	mA
I <sub>L</sub>	latching current	V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <a href="#">Fig. 10</a>	-	-	10	mA
		V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; <a href="#">Fig. 10</a>	-	-	20	mA
		V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; <a href="#">Fig. 10</a>	-	-	10	mA
		V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2- G+; T <sub>j</sub> = 25 °C; <a href="#">Fig. 10</a>	-	-	10	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 11</a>	-	-	10	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 1.4 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 12</a>	-	1.3	1.6	V
V <sub>GT</sub>	gate trigger voltage	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 13</a>	-	-	1	V
		V <sub>D</sub> = 800 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 125 °C; <a href="#">Fig. 13</a>	0.2	-	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 800 V; T <sub>j</sub> = 125 °C	-	-	0.5	mA
<b>Dynamic characteristics</b>						
dV <sub>D</sub> /dt	rate of rise of off-state voltage	V <sub>DM</sub> = 536 V; T <sub>j</sub> = 110 °C; (V <sub>DM</sub> = 67% of V <sub>DRM</sub> ); exponential waveform; gate open circuit; <a href="#">Fig. 14</a>	20	-	-	V/μs
dV <sub>com</sub> /dt	rate of change of commutating voltage	V <sub>D</sub> = 400 V; T <sub>j</sub> = 110 °C; dI <sub>com</sub> /dt = 0.44 A/ms; gate open circuit	1	-	-	V/μs



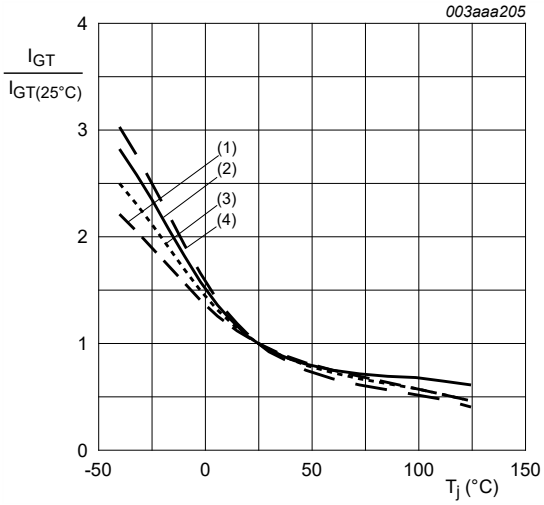


Fig. 9. Normalized gate trigger current as a function of junction temperature

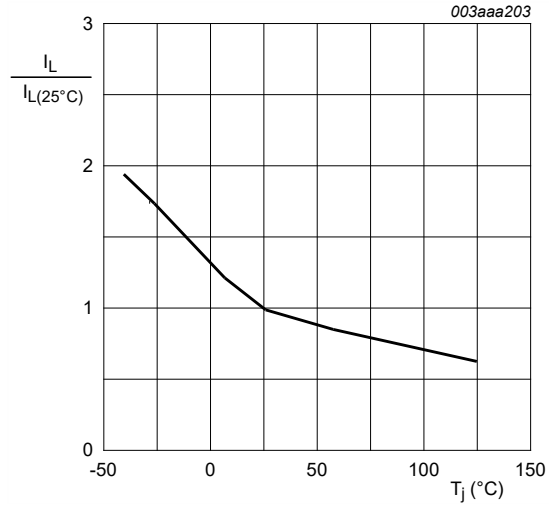


Fig. 10. Normalized latching current as a function of junction temperature

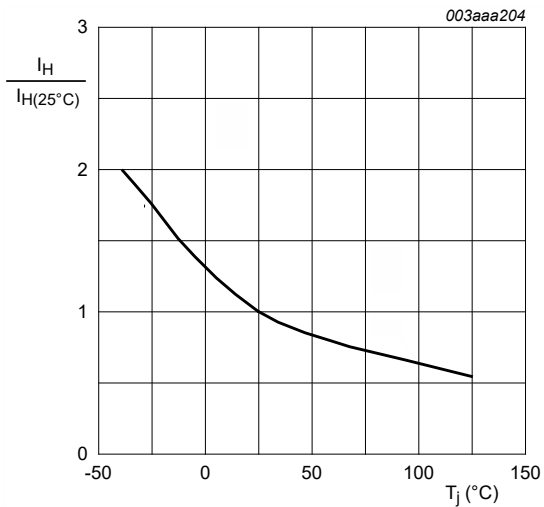
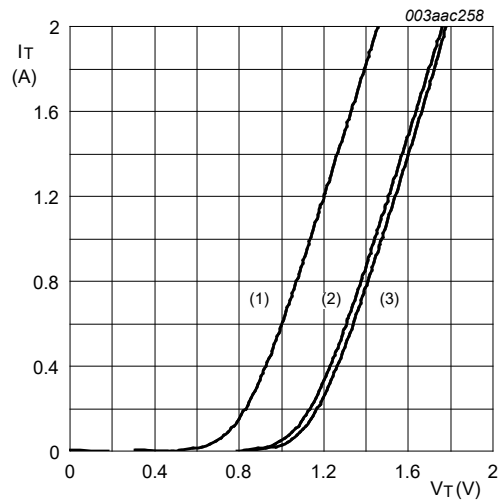


Fig. 11. Normalized holding current as a function of junction temperature



$V_o = 1.13\text{ V}$   
 $R_s = 0.31\ \Omega$

Fig. 12. On-state current as a function of on-state voltage

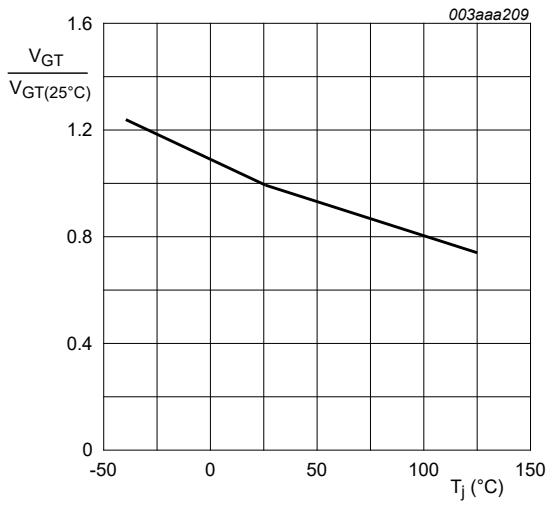
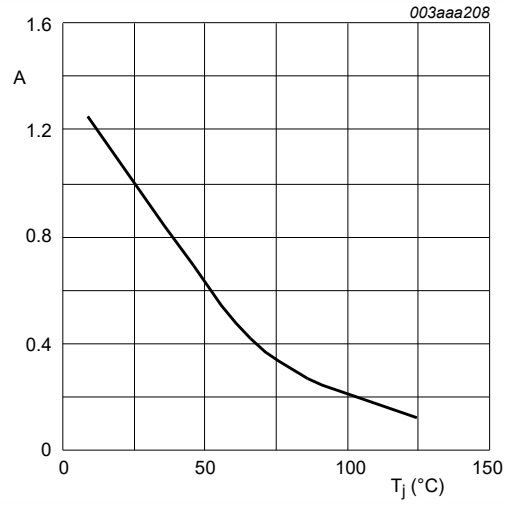


Fig. 13. Normalized gate trigger voltage as a function of junction temperature



$$A = \frac{dV_D(T_j \text{ } ^\circ\text{C}) / dt}{dV_D(25 \text{ } ^\circ\text{C}) / dt}$$

Fig. 14. Normalized critical rate of rise of off-state voltage as a function of junction temperature; typical values

### 10. Package outline

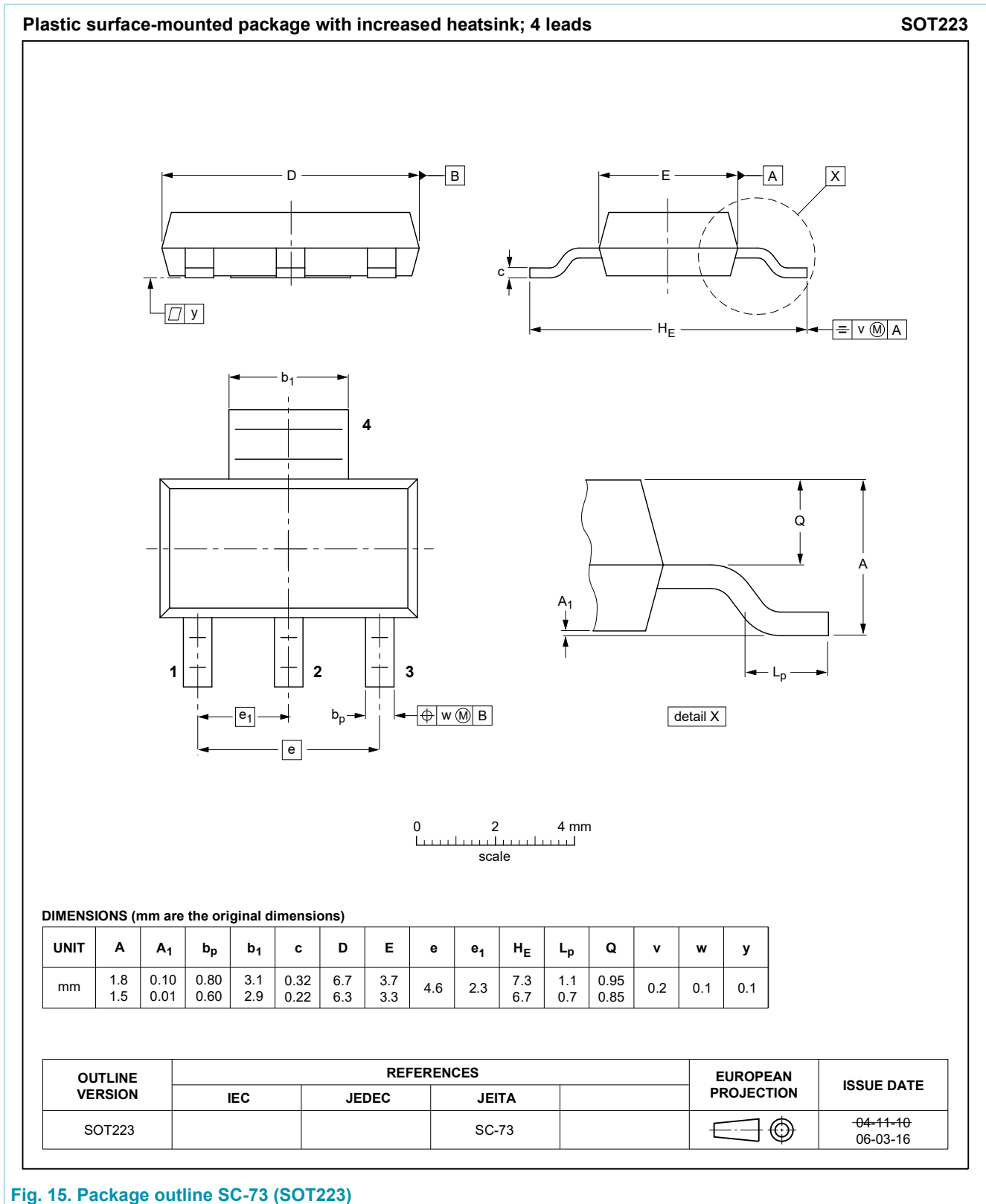


Fig. 15. Package outline SC-73 (SOT223)

## 11. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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For sales office addresses, please send an email to: [salesaddresses@ween-semi.com](mailto:salesaddresses@ween-semi.com)  
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